Complementary NPN-PNP Silicon Power Bipolar Transistors

The MJW3281A and MJW1302A are PowerBase[™] power transistors for high power audio, disk head positioners and other linear applications.

Features

- Designed for 100 W Audio Frequency
- Gain Complementary:
 - Gain Linearity from 100 mA to 7 A $h_{FE} = 45$ (Min) @ $I_C = 8$ A
- Low Harmonic Distortion
- High Safe Operation Area 1 A/100 V @ 1 Second
- High f_T 30 MHz Typical
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	230	Vdc
Collector-Base Voltage	V _{CBO}	230	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V _{CEX}	230	Vdc
Collector Current – Continuous – Peak (Note 1)	Ι _C	15 25	Adc
Base Current – Continuous	Ι _Β	1.5	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	PD	200 1.43	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.625	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.



TO-247 CASE 340L



ON Semiconductor®

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15 AMPERES

COMPLEMENTARY

SILICON POWER TRANSISTORS

230 VOLTS 200 WATTS

= Year

- WW = Work Week G
 - = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJW3281A	TO-247	30 Units/Rail
MJW3281AG	TO–247 (Pb–Free)	30 Units/Rail
MJW1302A	TO-247	30 Units/Rail
MJW1302AG	TO-247 (Pb-Free)	30 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	
Collector-Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	230	_	_	Vdc
Collector Cutoff Current (V_{CB} = 230 Vdc, I _E = 0)	I _{CBO}	-	-	50	μAdc
Emitter Cutoff Current ($V_{EB} = 5 \text{ Vdc}, I_C = 0$)	I _{EBO}	-	_	5	μAdc
SECOND BREAKDOWN			•	•	
Second Breakdown Collector with Base Forward Biased (V _{CE} = 50 Vdc, t = 1 s (non-repetitive) (V _{CE} = 100 Vdc, t = 1 s (non-repetitive)	I _{S/b}	4 1			Adc
ON CHARACTERISTICS		•		I.	
$ \begin{array}{l} \text{DC Current Gain} \\ (I_C = 100 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}) \\ (I_C = 1 \text{ Adc}, V_{CE} = 5 \text{ Vdc}) \\ (I_C = 3 \text{ Adc}, V_{CE} = 5 \text{ Vdc}) \\ (I_C = 5 \text{ Adc}, V_{CE} = 5 \text{ Vdc}) \\ (I_C = 7 \text{ Adc}, V_{CE} = 5 \text{ Vdc}) \\ (I_C = 8 \text{ Adc}, V_{CE} = 5 \text{ Vdc}) \\ (I_C = 15 \text{ Adc}, V_{CE} = 5 \text{ Vdc}) \end{array} $	h _{FE}	50 50 50 50 50 45 12	125 - - 115 - 35	200 200 200 200 200 -	-
Collector-Emitter Saturation Voltage $(I_C = 10 \text{ Adc}, I_B = 1 \text{ Adc})$	V _{CE(sat)}	_	0.4	2	Vdc
Base–Emitter On Voltage ($I_C = 8 \text{ Adc}, V_{CE} = 5 \text{ Vdc}$)	V _{BE(on)}	-	_	2	Vdc
DYNAMIC CHARACTERISTICS	ł	•			
Current–Gain – Bandwidth Product (I _C = 1 Adc, V _{CE} = 5 Vdc, f _{test} = 1 MHz)	fT	-	30	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	_	_	600	pF

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS





Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.



Figure 14. Active Region Safe Operating Area

The data of Figures 13 and 14 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.



TYPICAL CHARACTERISTICS

Figure 15. MJW1302A Typical Capacitance



PACKAGE DIMENSIONS



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	20.32	21.08	0.800	8.30
В	15.75	16.26	0.620	0.640
С	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
Е	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45	5.45 BSC		BSC
Н	1.50	2.49	0.059	0.098
Ĺ	0.40	0.80	0.016	0.031
Κ	19.81	20.83	0.780	0.820
г	5.40	6.20	0.212	0.244
Ν	4.32	5.49	0.170	0.216
Ρ		4.50		0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

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